











LSF0101, LSF0102, LSF0108

ZHCSBY4I - DECEMBER 2013 - REVISED JULY 2019

适用于开漏和推挽应用的 LSF010x 1/2/8 通道汽车双向多电压电平 转换器

1 特性

- 无需方向引脚,即可提供双向电压转换
- 在不超过 30pF 的容性负载条件下支持最高达 100MHz 的

上行转换和超过 100MHz 的下行转换,在 50pF 的 容性负载条件下支持高达 40MHz 的上行/下行转换

- 可实现以下电压之间的双向电压电平转换
 - 0.95V ↔ 1.8/2.5/3.3/5 V
 - 1.2V ↔ 1.8/2.5/3.3/5V
 - 1.8V ↔ 2.5/3.3/5V
 - 2.5V ↔ 3.3/5V
 - 3.3V ↔ 5V
- 低待机电流
- 支持 TTL 的 5V 耐受 I/O 端口
- 低 R_{ON} 可提供较少的信号失真
- 针对 EN 为低电平的高阻抗 I/O 引脚
- 采用直通引脚以简化 PCB 布线
- 闩锁性能超过 100mA,符合 JESD 17 规范
- -40°C 至 125°C 工作温度范围

2 应用

- GPIO、MDIO、PMBus、SMBus、SDIO、 UART、I²C 和电信基础设施中的其他接口
- 企业系统
- 通信设备
- 个人电子产品
- 工业 参考设计

3 说明

LSF 系列器件支持双向电压转换,而且无需使用 DIR 引脚,最大限度降低了系统工作量(PMBus、I²C、SMBus 等)。LSF 系列器件在容性负载 ≤ 30pF 时最高支持 100MHz 的升压转换和 100MHz 以上的降压转换;在容性负载为 50pF 时最高支持 40MHz 的升压/降压转换,因此可支持更多的消费类或电信接口(MDIO或 SDIO)。

LSF 系列的 IO 端口能够耐受 5V 电压,因此与工业和电信应用中的 TTL 电平 兼容。LSF 系列极具灵活性,能够为每条通道设置不同电压转换电平。

器件信息⁽¹⁾

押门口心					
器件型号	封装 (引脚)	封装尺寸(标称值)			
LSF0101DRY	SON (6)	1.45mm x 1.00mm			
LSF0101DTQ	X2SON (6)	1.00mm x 0.80mm			
LSF0102DQE	X2SON (8)	1.40mm x 1.00mm			
LSF0102YZT	DSBGA (8)	1.90mm x 1.00mm			
LSF0102DCT	SM8 (8)	2.80mm x 2.95mm			
LSF0102DCU	超薄小外形尺寸封装 (VSSOP)(8)	2.30mm x 2.00mm			
LSF0108RKS	VQFN (20)	4.50mm x 2.50mm			
LSF0108PW	TSSOP (20)	4.40mm x 6.50mm			

(1) 如需了解所有可用封装,请参阅数据表末尾的可订购产品附录。

LSF0102 LSF0101 LSF0108 DTQ Package DRY Package YZT Package DOE Package RKS Package 20-Pin VQFN 6-Pin X2SON 6-Pin SON 8-Pin DSBGA 8-Pin X2SON Transparent Top View Transparent Top View **Bottom View** Transparent Top View Transparent Top View GND EN GND EN (1) [4] EN GND 1 GND A2 0 0 B2 [8] EN Vref_A 2 Vref_B 2) (19) Vref B Vref A <2¦ Vref_B Vref_A [5] 3> Vref_B A1 @ @ B1 Vref A A1 31 16 B1 3) (18 В1 Α1 A1 [3]: [6] B1 Vref A Vref B A2 33 151 B2 B1 A2 4 (17) B2 GND @ EN <u>(16</u> **A3** 5) R3 Thermal Pad 6) <u>(15</u> A4 B4 7) (14 A5 B5 8) (<u>13</u> B6 A6 **A7** 9) (12 B7 A8 B8



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4 修订历史记录

注: 之前版本的页码可能与当前版本有所不同。

Changes from Revision H (June 2019) to Revision I **Page** Changes from Revision G (February 2016) to Revision H **Page** 已添加 在"器件信息"表中针对 DTQ 封装添加了预告信息注释 1 Changes from Revision F (October 2015) to Revision G **Page** Page Changes from Revision E (July 2015) to Revision F 已更改 特性 从"支持 100MHz 以上的高速转换"改为"容性负载 ≤ 30pF 时,支持最高 100MHz 的升压转换和 100MHz





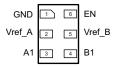
Changes from Revision D (October 2014) to Revision E	Page
己删除 特性中的"最大传播延迟低于 1.5ns"。	1
 已删除 特性中的"最大传播延迟低于 1.5ns"。 Updated ESD Ratings table. Increased MAX value for T_A, Operating free-air temperature, from 85°C to 125°C. Changes from Revision C (May 2014) to Revision D 已将双向电压电平转换从 1.0 改为 0.95 已更改 已更改 YZT 封装以修正视图错误。 Changed YZT package to fix view error. Added pin numbers to Pin Functions table. Added Vref_A footnote. Changes from Revision B (May 2014) to Revision C 已将 LSF0108 状态由"产品预览"改为"量产数据"。 	5
Changes from Revision C (May 2014) to Revision D	Page
已将双向电压电平转换从 1.0 改为 0.95	1
• 己更改 己更改 YZT 封装以修正视图错误。	1
Changed YZT package to fix view error.	4
Added pin numbers to Pin Functions table	4
Added Vref_A footnote.	13
Changes from Revision B (May 2014) to Revision C	Page
己将 LSF0108 状态由"产品预览"改为"量产数据"。	1
己更新文档标题	
Updated Handling Ratings table.	5
Changes from Revision A (January 2014) to Revision B	Page
• 在数据表中添加了 LSF0108。	1
Changes from Original (December 2013) to Revision A	Page
• 已更新产品型号。	1
Updated Electrical Characteristics table	6



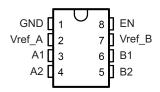
5 Pin Configuration and Functions

Pinout drawings are not to scale.

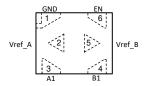




LSF0102 DCT or DCU Package 8-Pin SM8 or VSSOP Top View



LSF0101 DTQ Package 6-Pin X2SON Transparent Top View



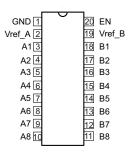
LSF0102 DQE Package 8-Pin X2SON Transparent Top View

GND	111	<u>_8</u>	EN
Vref_A	 	<u>_7</u>	Vref_B
A1	3_1	<u>_6</u>	B1
A2	4_	<u>_5</u>	B2

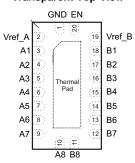
LSF0102 YZT Package 8-Pin DSBGA Bottom View

A2	① ₄	502	B2
A1	© 3	6©2	B1
Vref_A	® 2	7 B2	Vref_B
A2 A1 Vref_A GND	A1 1	8 (A2)	EN

LSF0108 PW Package 20-Pin TSSOP Top View



LSF0108 RKS Package 20-Pin VQFN Transparent Top View



Pin Functions

		PIN					
NAME	DCT, DCU, DQE, YZT NO.	DRY, DTQ NO.	PW or RKS NO.	I/O	DESCRIPTION		
An	3, 4	3	3 to 10	I/O	Auto Bidirectional Data part		
Bn	6, 5	4	18 to 11	I/O	Auto-Bidirectional Data port		
EN	8	6	20	I	Enable input; connect to Vref_B and pull-up through a high resist (200 k Ω). See Using the Enable Pin with the LSF Family		
GND	1	1	1	_	Ground		
Vref_A	2	2	2	_	Reference supply voltage.		
Vref_B	7	5	19	_	For proper device biasing, see <i>Application and Implementation</i> and Understanding the Bias Circuit for the LSF Family.		



6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature (unless otherwise noted)

				MIN	MAX	UNIT
V_{I}	Input voltage (2)			-0.5	7	V
V _{I/O}	Input/output voltage ⁽²⁾			-0.5	7	V
	Continuous channel current				128	mA
I _{IK}	Input clamp current	V	< 0		-50	mA
TJ	Junction Temperature				150	°C
T _{stg}	Storage temperature range			-65	150	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	\/
V _(ESD)	discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _{I/O}	Input/output voltage	0	5	V
V _{ref_A/B/EN}	Reference voltage	0	5	V
I _{PASS}	Pass transistor current		64	mA
T _A	Operating free-air temperature	-40	125	°C

²⁾ The input and input/output negative-voltage ratings may be exceeded if the input and input/output clamp-current ratings are observed.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions.



6.4 Thermal Information: LSF0101, LSF0108

THERMAL METRIC ⁽¹⁾		LSF0	LSF0101		LSF0108	
		DTQ (X2SON)	DRY (SON)	RKS (VQFN)	PW (TSSOP)	UNIT
		6 PINS	6 PINS	20 PINS	20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	294.4	407.0	49.3	106.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	188.9	285.2	45.9	41.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	216.8	271.6	20.6	57.6	°C/W
ΨЈТ	Junction-to-top characterization parameter	26.5	113.5	2.5	4.2	°C/W
ΨЈВ	Junction-to-board characterization parameter	216.0	271.0	20.6	47.0	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	3.4	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

6.5 Thermal Information: LSF0102

		LSF0102				
	THERMAL METRIC ⁽¹⁾		DCT (SM8)	DQE (X2SON)	YZT (DSBGA)	UNIT
		8 PINS	8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	210.1	189.6	246.5	125.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	89.1	119.6	149.1	1.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	88.8	102.1	100.0	62.7	°C/W
ΨЈТ	Junction-to-top characterization parameter	8.3	44.5	17.1	3.4	°C/W
ΨЈВ	Junction-to-board characterization parameter	88.4	101.0	99.8	62.7	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	n/a	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.

6.6 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TE	ST CONDITIONS	MIN TYP ⁽¹⁾	MAX	UNIT
V _{IK}	$I_1 = -18 \text{ mA},$	V _{EN} = 0			-1.2	V
I _{IH}	V _I = 5 V	V _{EN} = 0			5.0	μΑ
I _{CC}	$V_{ref_B} = V_{EN} = 5$	$.5 \text{ V}, \text{ V}_{\text{ref}_A} = 4.5$	V or 1 V, $I_O = 0$, $V_I = V_{CC}$ or GND	1		μΑ
C _{I(ref_A/B/EN)}	$V_I = 3 V \text{ or } 0$			11		pF
C _{io(off)}	$V_0 = 3 \text{ V or } 0,$	$V_{EN} = 0$		4.0	6.0	pF
C _{io(on)}	$V_0 = 3 \text{ V or } 0,$	$V_{EN} = 3 V$		10.5	12.5	pF
			$V_{ref_A} = 3.3 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$	8.0		
	$V_I = 0$,	$I_O = 64 \text{ mA}$	$V_{ref_A} = 1.8 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$	9.0		Ω
			$V_{ref_A} = 1.0 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$	10		
	$V_1 = 0$,	$I_0 = 32 \text{ mA}$	$V_{ref_A} = 1.8 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$	10		Ω
$r_{on}^{(2)}$	$V_1 = U$	1 ₀ = 32 IIIA	$V_{ref_A} = 2.5 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$	15		22
	$V_I = 1.8 V,$	$I_O = 15 \text{ mA}$	$V_{ref_A} = 3.3 \text{ V}; V_{ref_B} = V_{EN} = 5 \text{ V}$	9.0		Ω
	$V_I = 1.0 V,$	$I_O = 10 \text{ mA}$	$V_{ref_A} = 1.8 \text{ V}; V_{ref_B} = V_{EN} = 3.3 \text{ V}$	18		Ω
	$V_I = 0 V$,	$I_O = 10 \text{ mA}$	$V_{ref_A} = 1.0 \text{ V}; V_{ref_B} = V_{EN} = 3.3 \text{ V}$	20		Ω
	$V_I = 0 V$,	$I_O = 10 \text{ mA}$	$V_{ref_A} = 1.0 \text{ V}; V_{ref_B} = V_{EN} = 1.8 \text{ V}$	30		Ω

 ⁽¹⁾ All typical values are at T_A = 25°C.
 (2) Measured by the voltage drop between the A and B pins at the indicated current through the switch. On-state resistance is determined by the lowest voltage of the two (A or B) pins.



6.7 LSF0101/02 AC Performance (Translating Down) Switching Characteristics , V_{GATE} = 3.3 V

over recommended operating free-air temperature range, $V_{GATE} = 3.3 \text{ V}$, $V_{IH} = 3.3 \text{ V}$, $V_{IL} = 0$, and $V_{M} = 1.15 \text{ V}$ (unless otherwise noted) (see Figure 2)

DADAMETED	EDOM (INDUT)	TO (OUTPUT)	C _L = 50 pF		C _L = 30 pF		C _L = 15 pF		UNIT	
PARAMETER	FROM (INPUT)	TO (OUTPUT)	TYP	MAX	TYP	MAX	TYP	MAX	UNIT	
t _{PLH}	A or D	D or A	1.1		0.7		0.3			
t _{PHL}	A or B	B or A	1.2		0.8		0.4		ns	

6.8 LSF0108 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 3.3 V

over recommended operating free-air temperature range, $V_{GATE} = 3.3 \text{ V}$, $V_{IH} = 3.3 \text{ V}$, $V_{IL} = 0$, and $V_{M} = 1.15 \text{ V}$ (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50 pF		C _L = 30 pF		C _L = 15 pF		UNIT	
PARAMETER	FROW (INPUT)	10 (001701)	TYP M	AX	TYP	MAX	TYP	MAX	UNII	
t _{PLH}	A or D	D or 4	1.9		1.4		0.75		20	
t _{PHL}	A or B	B or A	2		1.5		0.85		ns	

6.9 LSF0101/02 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, $V_{GATE} = 2.5 \text{ V}$, $V_{IH} = 2.5 \text{ V}$, $V_{IL} = 0$, and $V_{M} = 0.75 \text{ V}$ (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50 pF		C _L = 30 pF		C _L = 15 pF		UNIT
PARAMETER	PROM (INPUT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	ONIT
t _{PLH}	A or D	B or A	1.2		0.8		0.35		ns
t _{PHL}	A or B		1.3		1		0.5		

6.10 LSF0108 AC Performance (Translating Down) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, $V_{GATE} = 2.5 \text{ V}$, $V_{IH} = 2.5 \text{ V}$, $V_{IL} = 0$, and $V_{M} = 0.75 \text{ V}$ (unless otherwise noted) (see Figure 2)

DADAMETED	EDOM (INDUT)	TO (OUTPUT)	C _L = 50 pF		C _L = 30 pF		C _L = 15 pF		UNIT
PARAMETER	FROM (INPUT)	TO (OUTPUT)	TYP	MAX	TYP	MAX	TYP	MAX	UNII
t _{PLH}	A or D	D or A	2		1.45		0.8		20
t _{PHL}	A or B	B or A	2.1		1.55		0.9		ns

6.11 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, $V_{GATE} = 3.3 \text{ V}$

over recommended operating free-air temperature range, $V_{GATE} = 3.3 \text{ V}$, $V_{IH} = 2.3 \text{ V}$, $V_{IL} = 0$, $V_{T} = 3.3 \text{ V}$, $V_{M} = 1.15 \text{ V}$ and $R_{L} = 300$ (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50 pF		C _L = 30 pF		C _L = 15 pF		UNIT
PARAMETER	PROW (INPUT)	10 (001F01)	TYP	MAX	TYP	MAX	TYP	MAX	UNII
t _{PLH}	A or D	B or A	1		0.8		0.4		20
t _{PHL}	A or B		1		0.9		0.4		ns

6.12 LSF0108 AC Performance (Translating Up) Switching Characteristics, $V_{GATE} = 3.3 \text{ V}$

over recommended operating free-air temperature range, $V_{GATE} = 3.3 \text{ V}$, $V_{IH} = 2.3 \text{ V}$, $V_{IL} = 0$, $V_{T} = 3.3 \text{ V}$, $V_{M} = 1.15 \text{ V}$ and $R_{L} = 300$ (unless otherwise noted) (see Figure 2)

DADAMETED	EDOM (INDUT)	TO (OUTDUT)	C _L = 50 pF		C _L = 30 pF		C _L = 15 pF		UNIT
PARAMETER	FROM (INPUT)	TO (OUTPUT)	TYP	MAX	TYP	MAX	TYP	MAX	UNIT
t _{PLH}	A or B	D or A	2.1		1.55		0.9		
t _{PHL}	AOIB	B or A	2.2		1.65		1		ns



6.13 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, V_{GATE} = 2.5 V

over recommended operating free-air temperature range, $V_{GATE} = 2.5 \text{ V}$, $V_{IH} = 1.5 \text{ V}$, $V_{IL} = 0$, $V_{T} = 2.5 \text{ V}$, $V_{M} = 0.75 \text{ V}$ and $R_{L} = 300$ (unless otherwise noted) (see Figure 2)

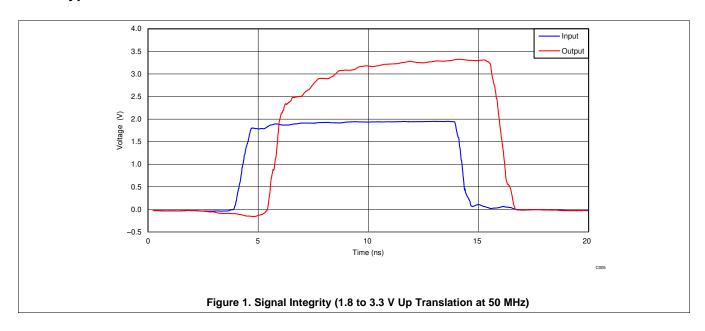
PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50 pF		C _L = 30 pF		C _L = 15 pF		UNIT	
PARAMETER	PROW (INPUT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	UNII	
t _{PLH}	A or D	D or A	1.1		0.9		0.45		20	
t _{PHL}	A or B	B or A	1.3		1.1		0.6		ns	

6.14 LSF0108 AC Performance (Translating Up) Switching Characteristics, $V_{GATE} = 2.5 \text{ V}$

over recommended operating free-air temperature range, $V_{GATE} = 2.5 \text{ V}$, $V_{IH} = 1.5 \text{ V}$, $V_{IL} = 0$, $V_{T} = 2.5 \text{ V}$, $V_{M} = 0.75 \text{ V}$ and $R_{L} = 300$ (unless otherwise noted) (see Figure 2)

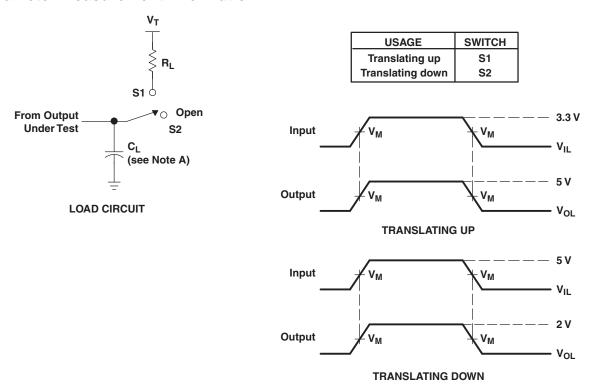
PARAMETER	FROM (INPUT)	TO (OUTPUT)	C _L = 50 pF		C _L = 30 pF		C _L = 15 pF		UNIT	
PARAMETER	PROW (INPUT)	10 (001701)	TYP	MAX	TYP	MAX	TYP	MAX	UNII	
t _{PLH}	A or D	B or A	1.8		1.35		0.8			
t _{PHL}	A or B		1.9		1.45		0.9		ns	

6.15 Typical Characteristics





7 Parameter Measurement Information



NOTES: A. C_L includes probe and jig capacitance.

- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2$ ns.
- C. The outputs are measured one at a time, with one transition per measurement.

Figure 2. Load Circuit for Outputs



8 Detailed Description

8.1 Overview

The LSF family can be used in level-translation applications for interfacing devices or systems operating with one another, that operate at different interface voltages. The LSF family is ideal for use in applications where an open-drain driver is connected to the data I/Os. With appropriate pull-up resistors and layout, LSF can achieve 100 MHz. The LSF family can also be used in applications where a push-pull driver is connected to the data I/Os. For an overview of device setup and operation, see *The Logic Minute* training series on *Understanding the LSF Family of Bidirectional, Multi-Voltage Level Translators*.

8.2 Functional Block Diagrams

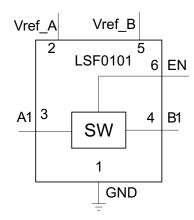


Figure 3. LSF0101 Functional Block Diagram

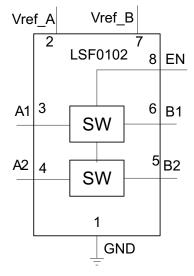


Figure 4. LSF0102 Functional Block Diagram



Functional Block Diagrams (continued)

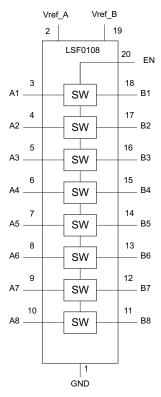


Figure 5. LSF0108 Functional Block Diagram

8.3 Feature Description

8.3.1 Auto Bidirectional Voltage Translation

All devices in the LSF family are auto bidirectional voltage level translators that are operational from 0.95 to 4.5 V on the Vref_A supply and from 1.8 to 5.5 V on the Vref_B supply. This allows bidirectional voltage translation between 0.95 V and 5.5 V without the need for a direction pin in open-drain or push-pull applications. LSF family supports level translation applications with transmission speeds greater than 100 Mbps for open-drain systems using a 30-pF capacitance and $250-\Omega$ pullup resistor. For additional details on the recommended setup and operation of the LSF family of devices, see the *Understanding the LSF Family of Bidirectional, Multi-Voltage Level Translators* training series.

8.3.2 Output Enable

To enable the I/O pins, the EN input should be tied directly to Vref_B during operation. To ensure the high impedance state during power-up, power-down, or during operation, the EN pin must be LOW. The EN pin should always be tied directly to the Vref_B pin and is recommended to be disabled by an open-drain driver without a pullup resistor. For additional details on how to use the enable pin, see the *Using the Enable Pin with the LSF Family* video.

Table 1. Enable Pin Function Table

INPUT EN ⁽¹⁾ PIN	Data Port State
Tied directly to Vref_B	An = Bn
L	Hi-Z

(1) EN is controlled by $V_{ref\ B}$ logic levels.



8.4 Device Functional Modes

For each channel (n), when either the An or Bn port is LOW, the switch provides a low impedance path between the An and Bn ports; the corresponding Bn or An port will be pulled LOW. The low R_{ON} of the switch allows connections to be made with minimal propagation delay and signal distortion.

When the signal is being driven from Bn to An and the Bn port is driven HIGH, the switch will be OFF, clamping the voltage on the An port to the voltage set by $Vref_A$. When the signal is being driven from A to B and the An port is HIGH, the switch will be OFF and the Bn port will then driven to a voltage higher than $Vref_A$ by the pullup resistor that is connected to the pull-up supply voltage ($V_{pu\#}$). This functionality allows seamless translation between higher and lower voltages selected by the user, without the need for directional control.

Refer to Table 1 for a summary of device operation. For additional details on the functional operation of the LSF family of devices, see the *Down Translation with the LSF Family* videos.

Signal Direction ⁽¹⁾	Input State	Switch State	Functionality
D to A (Down Translation)	B = LOW	ON (Low Impedance)	A-side voltage is pulled low through the switch to the B-side voltage
B to A (Down Translation)	B = HIGH	OFF (High Impedance)	A-side voltage is clamped at Vref_A ⁽²⁾
A to D (He Translation)	A = LOW	ON (Low Impedance)	B-side voltage is pulled low through the switch to the A-side voltage
A to B (Up Translation)	A = HIGH	OFF (High Impedance)	B-side voltage is clamped at Vref_A and then pulled up to the Vpu# supply voltage

⁽¹⁾ The downstream channel should not be actively driven through a low impedance driver, or else there may be bus contention.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LSF devices are able to perform voltage translation for open-drain or push-pull interfaces. Table 3 provides common interfaces and the corresponding device recommendation from the LSF family which supports the corresponding bit count.

Table 3. Voltage Translator for Common Interfaces

Part Name	Channel Number	Interface
LSF0101	1	GPIO
LSF0102	2	GPIO, MDIO, SMBus, PMBus, I ² C
LSF0108	8	GPIO, MDIO, SDIO, SVID, UART, SMBus, PMBus, I ² C, SPI

⁽²⁾ The A-side can have a pullup to Vref_A for additional current drive capability or may also be pulled above Vref_A with a pullup resistor. Specifications in the Recommended Operating Conditions should always be followed.



9.2 Typical Applications

9.2.1 Open-Drain Interface (I²C, PMBus, SMBus, GPIO)

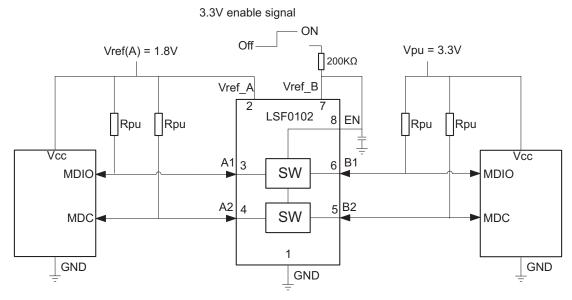


Figure 6. Typical Application Circuit for Open-Drain Translation (MDIO shown as an example)

9.2.1.1 Design Requirements

9.2.1.1.1 Enable, Disable, and Reference Voltage Guidelines

The LSF family has an EN input that is used to disable the device by setting EN LOW, placing all I/Os in the high-impedance state. Since the LSF family of devices are switch-type voltage translators, the power consumption is very low. TI recommends always enabling the LSF family for bidirectional applications (I²C, SMBus, PMBus, or MDIO).

	PARAMETER	MIN	TYP	MAX	UNIT
Vref_A ⁽¹⁾	reference voltage (A)	0.95		4.5	V
Vref_B	reference voltage (B)	Vref_A + 0.8		5.5	V
$V_{I(EN)}$	input voltage on EN pin	Vref_A + 0.8		5.5	V
Vpu	pull-up supply voltage	0		Vref_B	V

Table 4. Application Operating Condition

The 200 k Ω , pull-up resistor is required to allow Vref_B to regulate the EN input and properly bias the device for translation. For additional details on device biasing, see the *Understanding the Bias Circuit for the LSF Family* video. A filter capacitor on Vref_B is recommended. Also Vref_B and V_{I(EN)} are recommended to be 1.0 V higher than Vref_A for best signal integrity.

9.2.1.2 Detailed Design Procedure

9.2.1.2.1 Bidirectional Translation

For the bidirectional translation configuration (higher voltage to lower voltage or lower voltage to higher voltage), the EN input must be connected to Vref_B and both pins must be pulled up to the HIGH side Vpu through a pull-up resistor (typically 200 k Ω). This allows Vref_B to regulate the EN input and bias the channels for proper translation. A filter capacitor on Vref_B is recommended for a stable supply at the device. The master output driver can be push-pull or open-drain (pull-up resistors may be required) and the slave device output can be push-pull or open-drain (pull-up resistors are required to pull the Bn outputs to Vpu).

⁽¹⁾ Vref_A is required to be the lowest voltage level across all inputs and outputs.



If either output is push-pull, data must be unidirectional or the outputs must be tri-state and be controlled by some direction-control mechanism to prevent HIGH-to-LOW bus contention in either direction. If both outputs are open-drain, no direction control is needed.

When Vref_B is connected through a 200-k Ω resistor to a 3.3-V Vpu power supply and Vref_A is set 1.8 V, as shown in Figure 6, the A1 and A2 channels have a maximum output voltage equal to Vref_A, and the B1 and B2 channels have has a maximum output voltage equal to Vpu.

9.2.1.2.2 Pull-up Resistor Sizing

The pull-up resistor value needs to limit the current through the pass transistor when it is in the ON state to about 15 mA. This ensures a voltage drop of 260 mV to 350 mV to have a valid LOW signal on the downstream channel. If the current through the pass transistor is higher than 15 mA, the voltage drop is also higher in the ON state. To set the current through each pass transistor at 15 mA, calculate the pull-up resistor value using the following equation:

$$Rpu = (Vpu - 0.35 V) / 0.015 A$$
 (1)

Table 5 summarizes resistor values, reference voltages, and currents at 15 mA, 10 mA, and 3 mA. The resistor value shown in the +10% column (or a larger value) should be used to ensure that the voltage drop across the transistor is 350 mV or less. The external driver must be able to sink the total current from the resistors on both sides of the LSF family device at 0.175 V, although the 15 mA applies only to current flowing through the LSF family device.

15 mA 10 mA 3 mA V_{DPU} $+10\%^{(3)}(\Omega)$ $+10\%^{(3)}(\Omega)$ $+10\%^{(3)}(\Omega)$ NOMINAL (Ω) NOMINAL (Ω) NOMINAL (Ω) 512 5 V 310 341 465 1550 1705 3.3 V 197 217 295 325 983 1082 2.5 V 143 215 717 788 158 237 1.8 V 97 106 145 160 483 532 1.5 V 77 115 383 422 85 127 1.2 V 57 63 85 94 283 312

Table 5. Pull-up Resistor Values (1)(2)

9.2.1.3 Application Curve

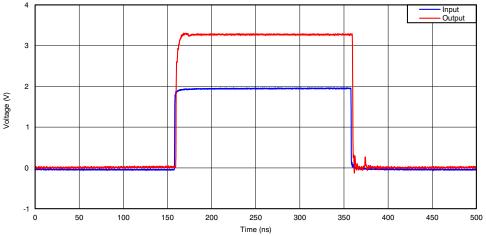


Figure 7. Open Drain Translation (1.8 V to 3.3 V at 2.5 MHz)

Calculated for V_{OI} = 0.35 V

⁽²⁾ Assumes output driver V_{OL} = 0.175 V at stated current

^{(3) +10%} to compensate for V_{DD} range and resistor tolerance



9.2.2 Mixed-Mode Voltage Translation

The supply voltage $(V_{pu\#})$ for each channel can be individually set with a pull-up resistor. An example of this mixed-mode multi-voltage translation is shown in Figure 8. For additional details on multi-voltage translation, see the *Multi-voltage Translation with the LSF Family* video.

With the Vref_B pulled up to 5V and Vref_A connected to 1.8V, all channels will be clamped to 1.8V at which point a pullup can be used to define the high level voltage for a given channel.

- Push-Pull Down Translation (5V to 1.8V): Channel 1 is an example of this setup. When B1 is 5V, A1 is clamped to 1.8V, and when B1 is LOW, A1 is driven LOW through the switch.
- Push-Pull Up Translation (1.8V to 5V): Channel 2 is an example of this setup. When A2 is 1.8V, the switch is high impedance and the B2 channel is pulled up to 5V. When A2 is LOW, B2 is driven LOW through the switch.
- Push-Pull Down Translation (3.3V to 1.8V): Channels 3 and 4 are examples of this setup. When either B3 or B4 are driven to 3.3V, A3 or A4 are clamped to 1.8V, and when either B3 or B4 are LOW, A3 or A4 are driven LOW through the switch.
- Open-Drain Bidirectional Translation (3.3V ↔ 1.8V): Channels 5 through 8 are examples of this setup. These channels are for bidirectional operation for I²C and MDIO to translate between 1.8V and 3.3V with open-drain drivers.

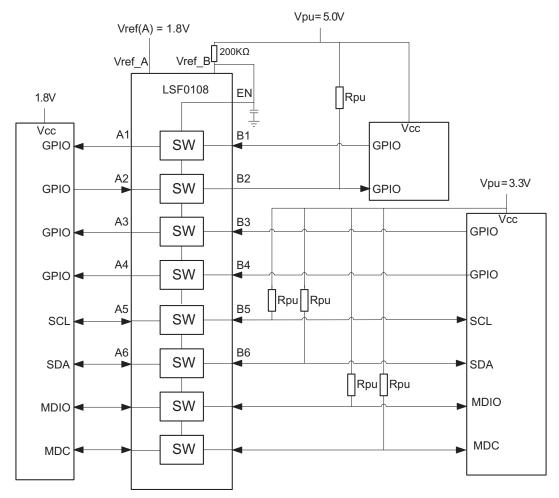


Figure 8. Multi-Voltage Translation with the LSF0108



10 Power Supply Recommendations

There are no power sequence requirements for the LSF family. For recommended operating voltages for all supply and input pins, see Table 6.

Table 6. Recommended Operating Voltages

	PARAMETER	MIN	TYP MAX	UNIT
Vref_A ⁽¹⁾	reference voltage (A)	0.95	4.5	V
Vref_B	reference voltage (B)	Vref_A + 0.8	5.5	V
$V_{I(EN)}$	input voltage on EN pin	Vref_A + 0.8	5.5	V
Vpu	pull-up supply voltage	0	Vref_B	V

⁽¹⁾ Vref_A is required to be the lowest voltage level across all inputs and outputs.

11 Layout

11.1 Layout Guidelines

Because the LSF family is a switch-type level translator, the signal integrity is highly related with a pull-up resistor and PCB capacitance condition.

- Short signal trace as possible to reduce capacitance and minimize stub from pull-up resistor.
- Place LSF close to high voltage side.
- Select the appropriate pull-up resistor that applies to translation levels and driving capability of transmitter.

11.2 Layout Example

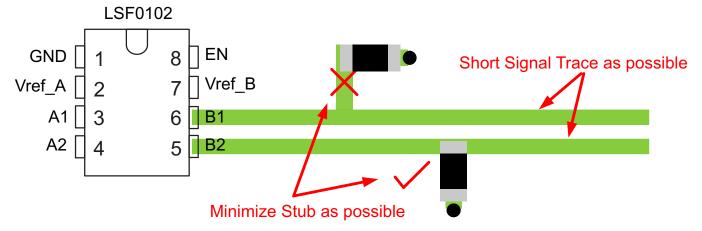


Figure 9. Short Trace Layout

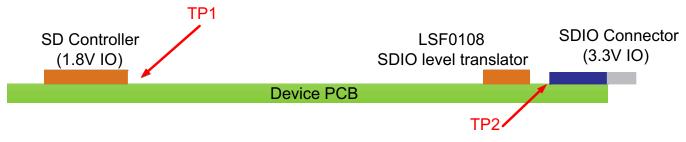


Figure 10. Device Placement



12 器件和文档支持

12.1 相关链接

下表列出了快速访问链接。类别包括技术文档、支持与社区资源、工具和软件,以及申请样片或购买产品的快速链接。

表 7. 相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持和社区	
LSF0101	LSF0101 单击此处		单击此处	单击此处	单击此处	
LSF0102	LSF0102 单击此处		单击此处	单击此处	单击此处	
LSF0108	LSF0108 单击此处		单击此处	单击此处	单击此处	

- 1. LSF 转换器系列评估模块
- 2. 有关了解 LSF 系列器件的 Logic Minute 视频培训系列
 - 简介 使用 LSF 系列进行电压电平转换
 - 了解 LSF 系列的偏置电路
 - 针对 LSF 系列使用使能引脚
 - LSF 系列的转换基础知识
 - 使用 LSF 系列进行下行转换
 - 使用 LSF 系列进行上行转换
 - 使用 LSF 系列进行多电压转换
 - 使用 LSF 系列进行单电源转换
- 3. 《使用 LSF 系列进行电压电平转换》应用手册
- 4. 《TXS、TXB 和 LSF 自动双向转换器的偏置要求》应用手册

12.2 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 商标

E2E is a trademark of Texas Instruments.

12.4 静电放电警告



这些装置包含有限的内置 ESD 保护。 存储或装卸时,应将导线一起截短或将装置放置于导电泡棉中,以防止 MOS 门极遭受静电损伤。

12.5 Glossary

SLYZ022 — TI Glossarv.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更,恕不另行通知,且不会对此文档进行修订。如需获取此数据表的浏览器版本,请查阅左侧的导航栏。





24-Jan-2021

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
LSF0101DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD	Samples
LSF0101DTQR	ACTIVE	X2SON	DTQ	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	FC	Samples
LSF0102DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	NG2 (S, Y)	Samples
LSF0102DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(G2, NG2J, NG2P, N G2S) NY	Samples
LSF0102DQER	ACTIVE	X2SON	DQE	8	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	RV	Samples
LSF0102YZTR	ACTIVE	DSBGA	YZT	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	RV	Samples
LSF0108PWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 125	LSF0108	Samples
LSF0108RKSR	ACTIVE	VQFN	RKS	20	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LSF0108	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



PACKAGE OPTION ADDENDUM

24-Jan-2021

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 27-May-2021

TAPE AND REEL INFORMATION





_		
		Dimension designed to accommodate the component width
	B0	Dimension designed to accommodate the component length
	K0	Dimension designed to accommodate the component thickness
ľ	W	Overall width of the carrier tape
ı	P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

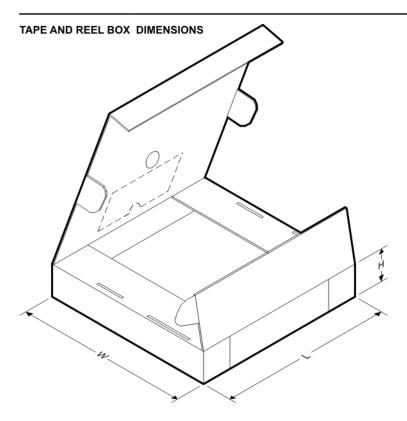


*All dimensions are nominal

All dimensions are nominal	_			1								
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LSF0101DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
LSF0101DTQR	X2SON	DTQ	6	3000	180.0	9.5	0.94	1.13	0.5	2.0	8.0	Q2
LSF0102DCTR	SM8	DCT	8	3000	177.8	12.4	3.45	4.4	1.45	4.0	12.0	Q3
LSF0102DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.25	3.4	1.0	4.0	8.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
LSF0102DQER	X2SON	DQE	8	5000	180.0	9.5	1.15	1.6	0.5	4.0	8.0	Q1
LSF0102YZTR	DSBGA	YZT	8	3000	180.0	8.4	1.02	2.02	0.75	4.0	8.0	Q1
LSF0108PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
LSF0108RKSR	VQFN	RKS	20	3000	177.8	12.4	2.73	4.85	1.03	4.0	12.0	Q1



www.ti.com 27-May-2021



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LSF0101DRYR	SON	DRY	6	5000	184.0	184.0	19.0
LSF0101DTQR	X2SON	DTQ	6	3000	189.0	185.0	36.0
LSF0102DCTR	SM8	DCT	8	3000	183.0	183.0	20.0
LSF0102DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
LSF0102DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
LSF0102DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
LSF0102DQER	X2SON	DQE	8	5000	184.0	184.0	19.0
LSF0102YZTR	DSBGA	YZT	8	3000	182.0	182.0	20.0
LSF0108PWR	TSSOP	PW	20	2000	364.0	364.0	27.0
LSF0108RKSR	VQFN	RKS	20	3000	202.0	201.0	28.0

DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



- : A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-187 variation CA.



DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.









- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.





NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).





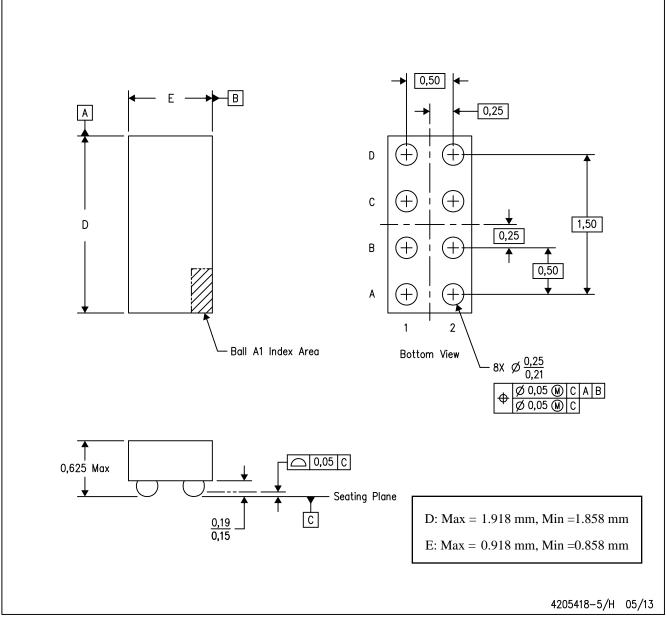
NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



YZT (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

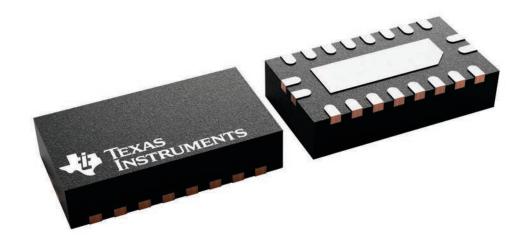
NanoFree is a trademark of Texas Instruments.



2.5 x 4.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

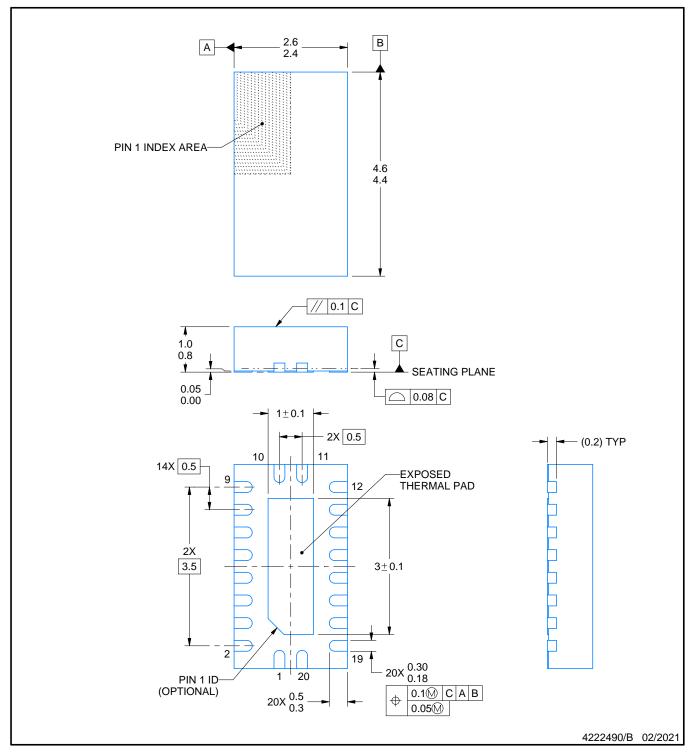
This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



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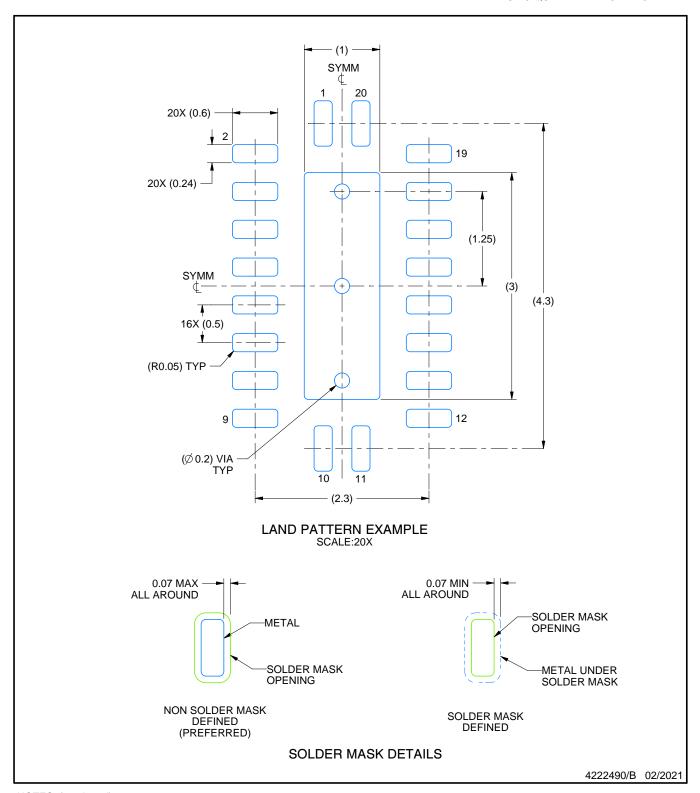
PLASTIC QUAD FLATPACK - NO LEAD



- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

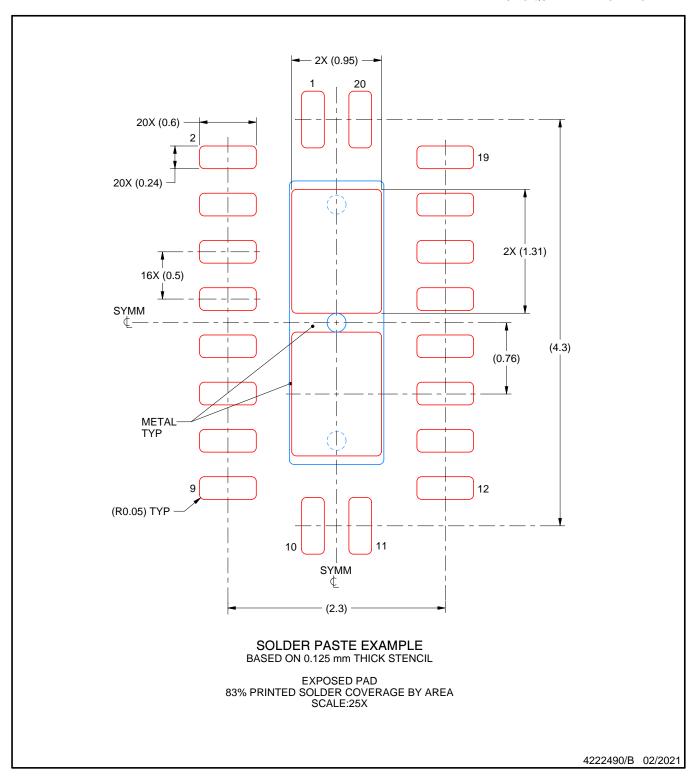


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



PLASTIC QUAD FLATPACK - NO LEAD

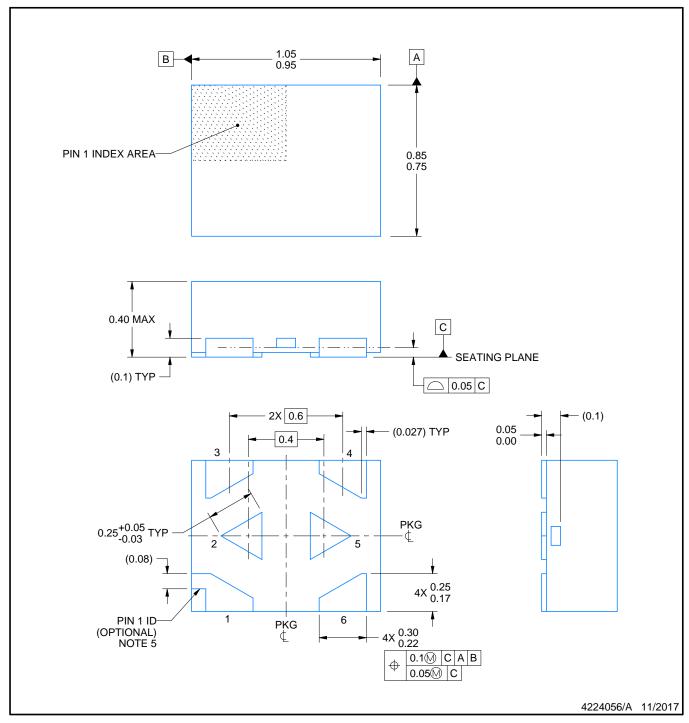


NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



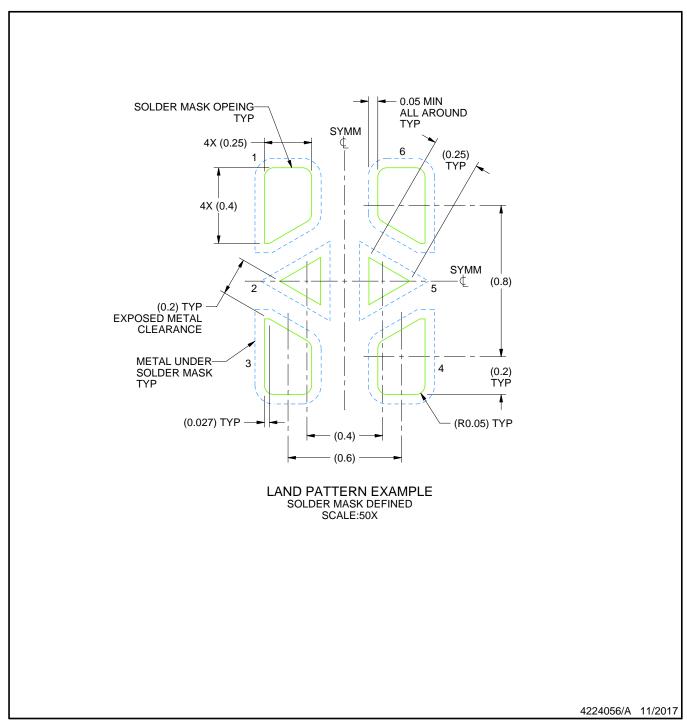




- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pads must be soldered to the printed circuit board for optimal thermal and mechanical performance.

 4. The size and shape of this feature may vary.
- 5. Features may not exist. Recommend use of pin 1 marking on top of package for orientation purposes.



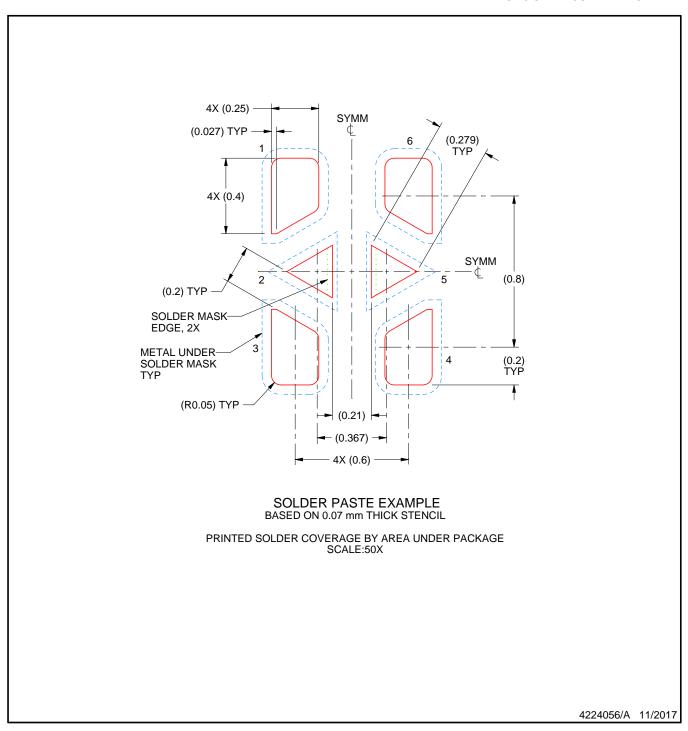


NOTES: (continued)



^{6.} This package is designed to be soldered to a thermal pads on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

^{7.} Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





SMALL OUTLINE PACKAGE



- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.



SMALL OUTLINE PACKAGE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
 C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.







- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This package complies to JEDEC MO-287 variation X2EAF.





NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).





NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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